

Silicon PNP Power Transistors

2SB1495

DESCRIPTION

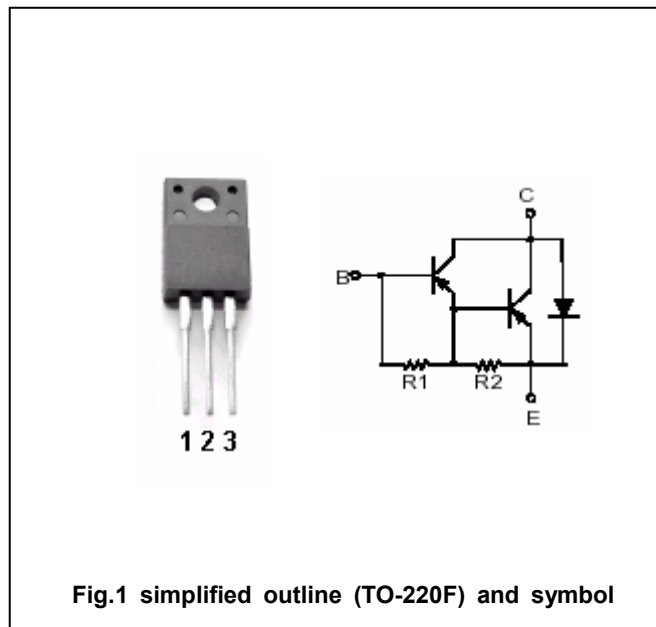
- With TO-220F package
- Complement to type 2SD2257
- High DC current gain.
- Low saturation voltage.
- DARLINGTON

APPLICATIONS

- High power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-8	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-5	A
I_B	Base current		-0.3	A
P_C	Collector dissipation	$T_C=25^\circ\text{C}$	20	W
		$T_a=25^\circ\text{C}$	2	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-1.5mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.5A; I _B =-1.5mA			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-8V; I _C =0			-4.0	mA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-2V	2000			
h _{FE-2}	DC current gain	I _C =-2A; V _{CE} =-2V	2000			

Switching times

t _{on}	Turn-on time	I _{B1} =-I _{B2} =-1.5mA V _{CC} =-30V, R _L =20Ω		0.5		μs
t _s	Storage time			1.0		μs
t _f	Fall time			0.4		μs

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PACKAGE OUTLINE

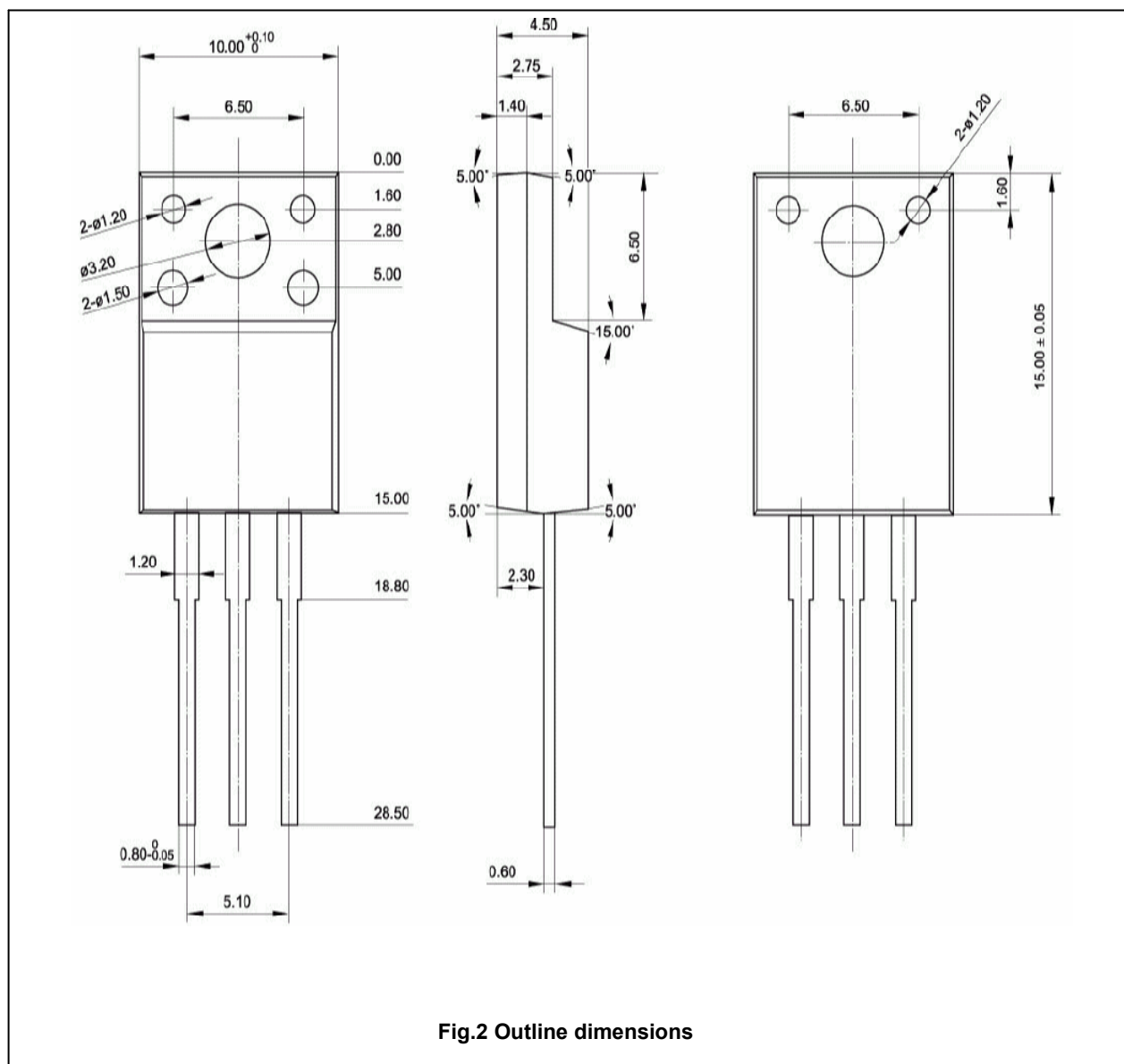


Fig.2 Outline dimensions